



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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N-Channel Power MOSFET

600V, 10A, 0.75Ω

FEATURES

- 100% UIS and R_g tested
- Advanced planar process
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

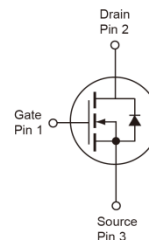
| PARAMETER | VALUE | UNIT |
|--------------------|-------|------|
| V_{DS} | 600 | V |
| $R_{DS(on)}$ (max) | 0.75 | Ω |
| Q_g | 33 | nC |

APPLICATIONS

- AC/DC LED Lighting
- Power Supply



ITO-220S



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| PARAMETER | SYMBOL | Limit | UNIT |
|--|----------------|---------------------------|------|
| Drain-Source Voltage | V_{DS} | 600 | V |
| Gate-Source Voltage | V_{GS} | ±30 | V |
| Continuous Drain Current (Note 1) | I_D | $T_C = 25^\circ\text{C}$ | 10 |
| | | $T_C = 100^\circ\text{C}$ | 6 |
| Pulsed Drain Current (Note 2) | I_{DM} | 30 | A |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ | P_{DTOT} | 45 | W |
| Single Pulse Avalanche Energy (Note 3) | E_{AS} | 422.5 | mJ |
| Single Pulse Avalanche Current (Note 3) | I_{AS} | 6.5 | A |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | - 55 to +150 | °C |

THERMAL PERFORMANCE

| PARAMETER | SYMBOL | Limit | UNIT |
|--|-----------------|-------|------|
| Junction to Case Thermal Resistance | $R_{\theta JC}$ | 2.8 | °C/W |
| Junction to Ambient Thermal Resistance | $R_{\theta JA}$ | 62 | °C/W |

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.

| ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted) | | | | | | |
|---|--|-------------------------------------|----------|------|-----------|---------------|
| PARAMETER | CONDITIONS | SYMBOL | MIN | TYP | MAX | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ | BV_{DSS} | 600 | -- | -- | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | $V_{GS(TH)}$ | 2.5 | 3.4 | 4.5 | V |
| Gate Body Leakage | $V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$ | I_{GSS} | -- | -- | ± 100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$ | I_{DSS} | -- | -- | 1 | μA |
| Drain-Source On-State Resistance (Note 4) | $V_{GS} = 10\text{V}, I_D = 2.5\text{A}$ | $R_{DS(on)}$ | -- | 0.67 | 0.75 | Ω |
| Forward Transconductance (Note 4) | $V_{DS} = 10\text{V}, I_D = 5\text{A}$ | g_{fs} | -- | 7 | -- | S |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | $V_{DS} = 480\text{V}, I_D = 5\text{A},$ $V_{GS} = 10\text{V}$ | Q_g | -- | 33 | -- | nC |
| Gate-Source Charge | | Q_{gs} | -- | 10 | -- | |
| Gate-Drain Charge | | Q_{gd} | -- | 12 | -- | |
| Input Capacitance | $V_{DS} = 50\text{V}, V_{GS} = 0\text{V},$ $f = 1.0\text{MHz}$ | C_{iss} | -- | 1652 | -- | μF |
| Output Capacitance | | C_{oss} | -- | 92 | -- | |
| Reverse Transfer Capacitance | | C_{rss} | -- | 11 | -- | |
| Gate Resistance | $f = 1.0\text{MHz}, \text{open drain}$ | R_g | 0.6 | 2.1 | 4.2 | Ω |
| Switching (Note 6) | | | | | | |
| Turn-On Delay Time | $V_{DD} = 300\text{V}, R_G = 5\Omega,$ $I_D = 5\text{A}, V_{GS} = 10\text{V}$ | $t_{d(on)}$ | -- | 14 | -- | ns |
| Turn-On Rise Time | | t_r | -- | 21 | -- | |
| Turn-Off Delay Time | | $t_{d(off)}$ | -- | 29 | -- | |
| Turn-Off Fall Time | | t_f | -- | 21 | -- | |
| Source-Drain Diode | | | | | | |
| Forward Voltage (Note 4) | $I_S = 5\text{A}, V_{GS} = 0\text{V}$ | V_{SD} | -- | -- | 1.4 | V |
| Reverse Recovery Time | $I_S = 5\text{A}$ | t_{rr} | -- | 262 | -- | ns |
| Reverse Recovery Charge | | $di_F/dt = 100\text{A}/\mu\text{s}$ | Q_{rr} | -- | 2.9 | -- |

Notes:

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. $L = 20\text{mH}, I_{AS} = 6.5\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

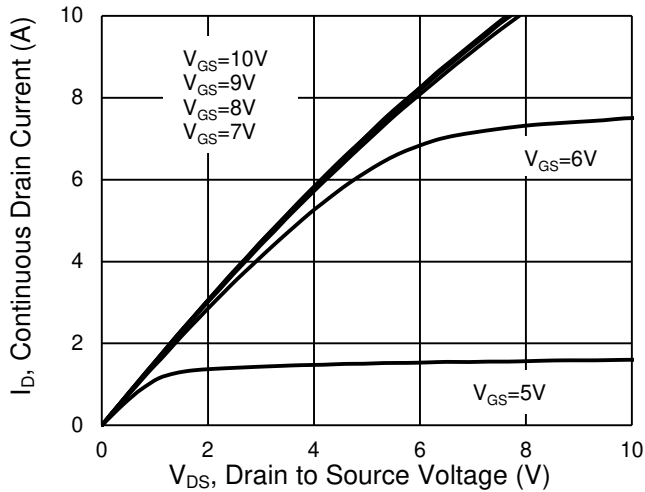
ORDERING INFORMATION

| PART NO. | PACKAGE | PACKING |
|-----------------|----------|--------------|
| TSM10NC60CF C0G | ITO-220S | 50pcs / Tube |

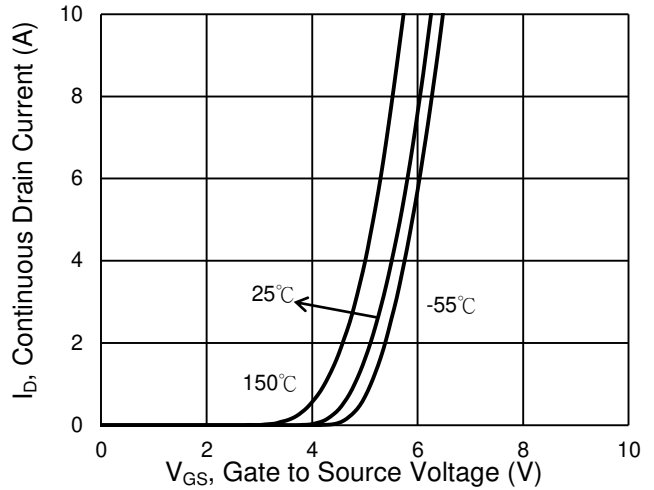
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

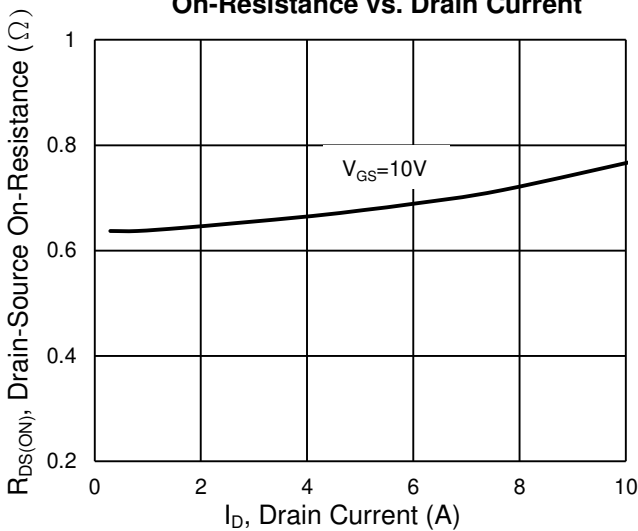
Output Characteristics



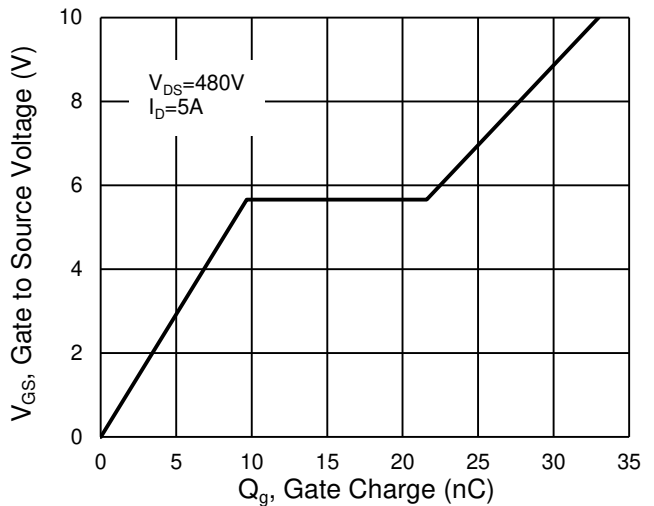
Transfer Characteristics



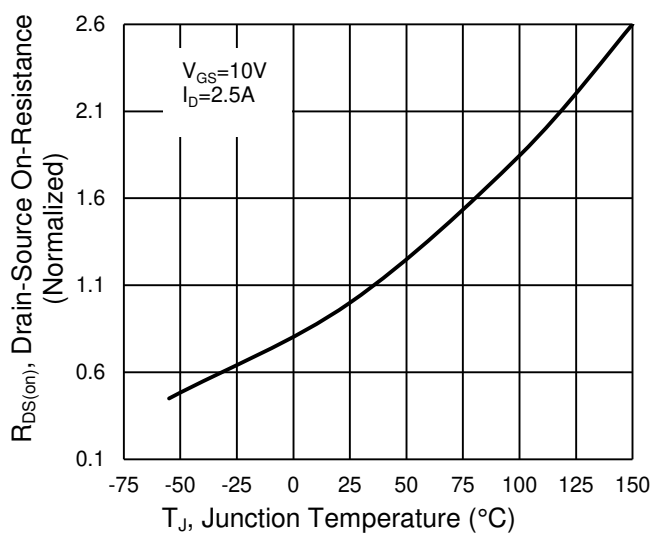
On-Resistance vs. Drain Current



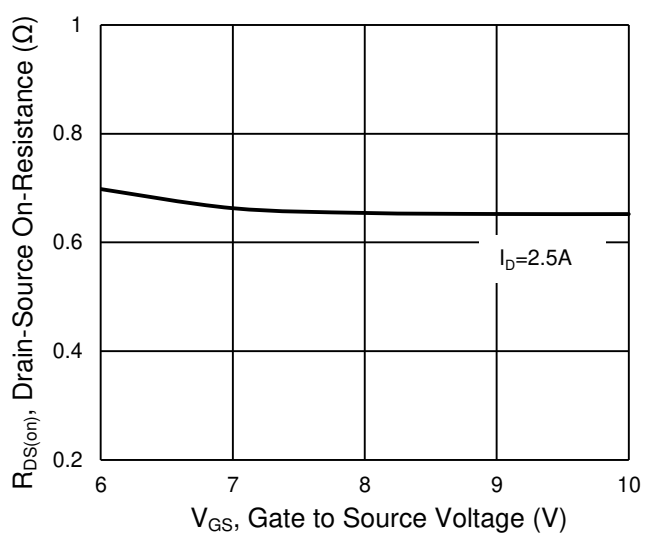
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



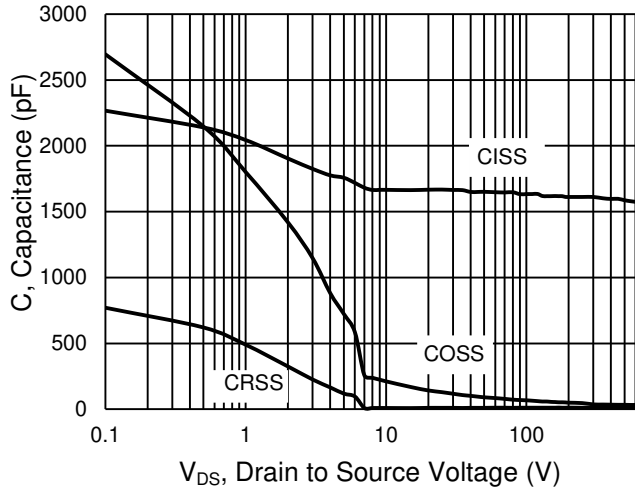
On-Resistance vs. Gate-Source Voltage



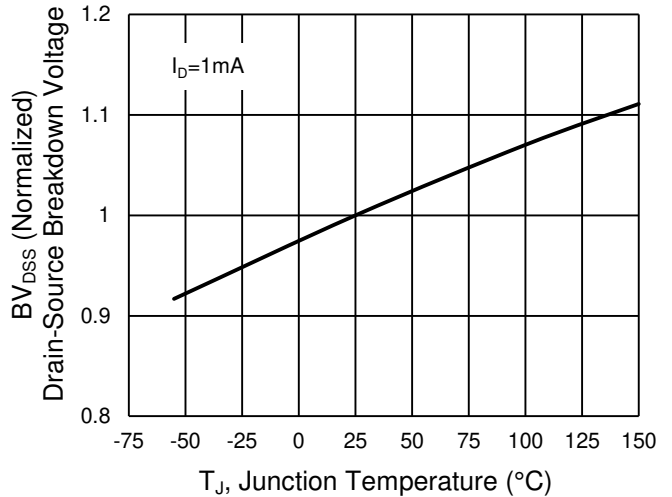
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

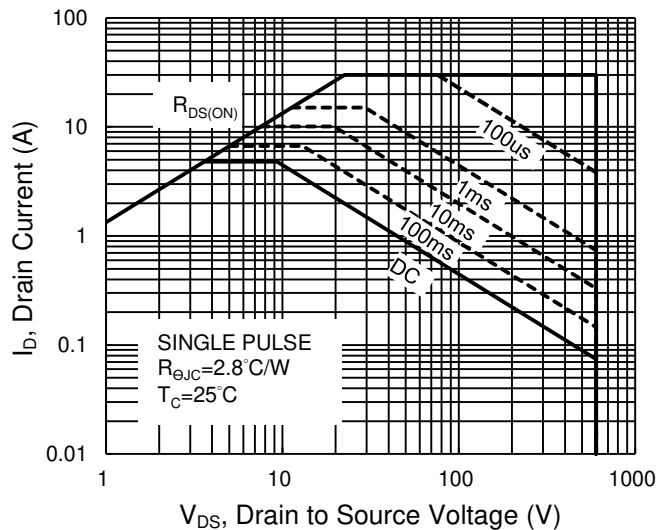
Capacitance vs. Drain-Source Voltage



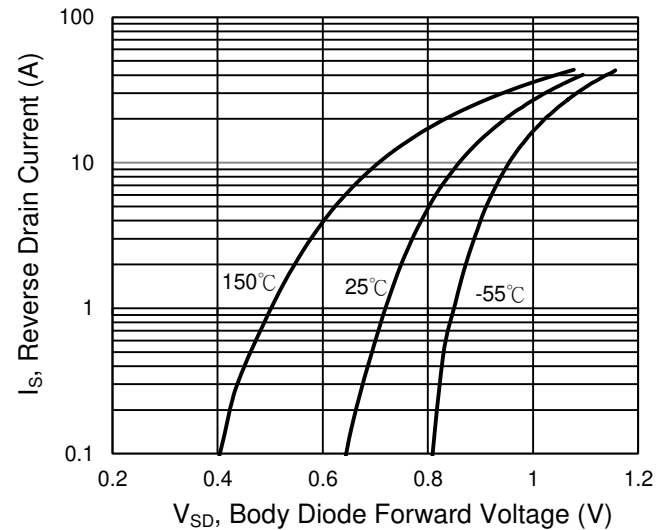
BV_{DSS} vs. Junction Temperature



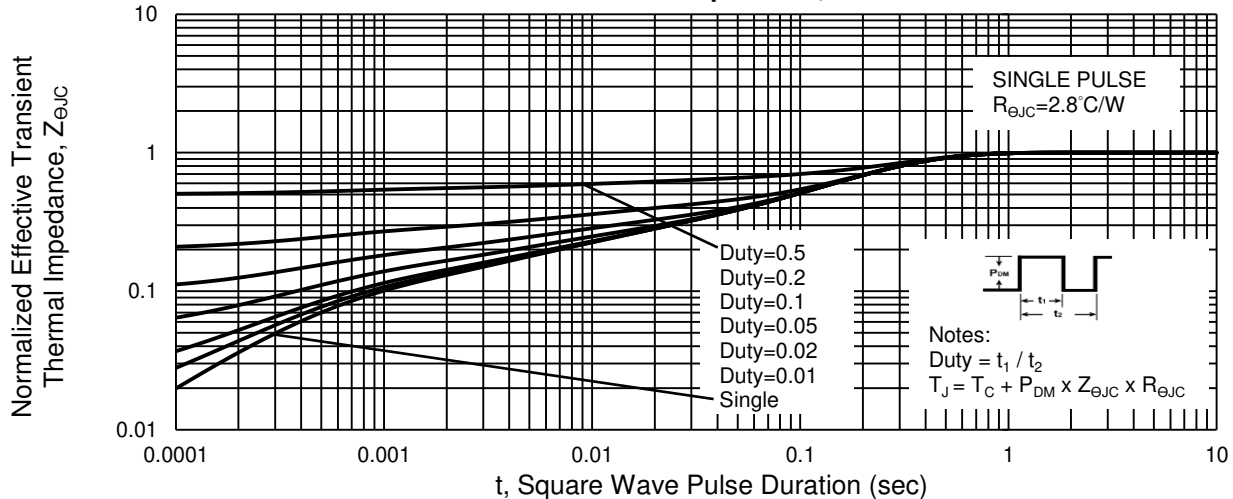
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

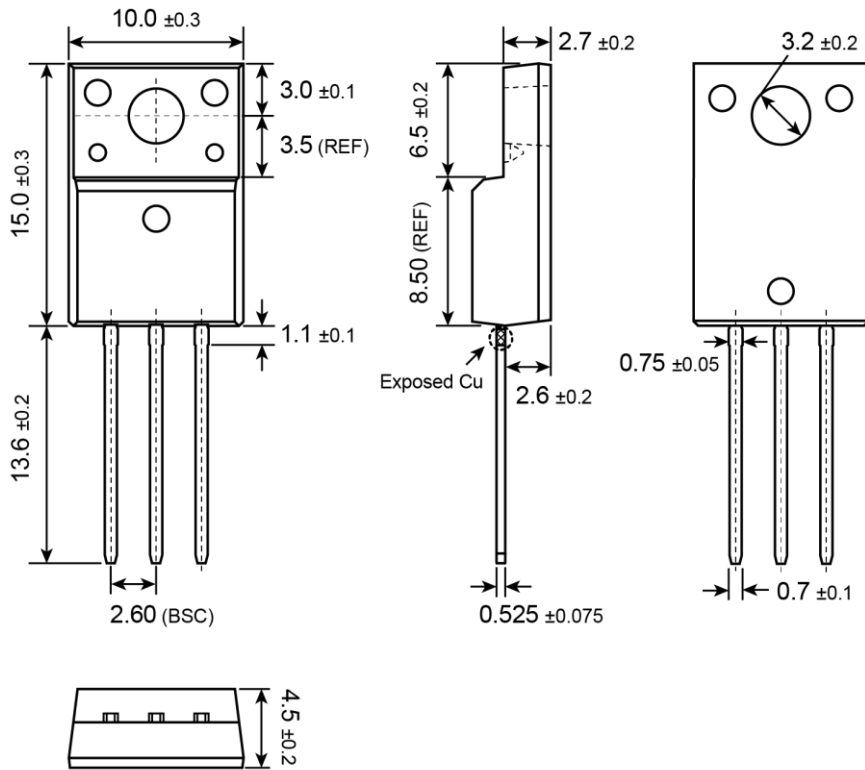


Normalized Thermal Transient Impedance, Junction-to-Case



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

ITO-220S



MARKING DIAGRAM



- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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